YJ Planar Fast Recovery Diode Die Specification

400V 75A, Fast recovery diode die based on silicon planar process
Part No.: FRD75A400AS-290A

Main Products Characterstics

Maximum Ratings

Parameter	Symbol	Rating
Repetitive peak reverse voltage	V_{RRM}	400V
Average forward current	$I_{F(AV)}$	75A
	I_{FSM}	

Static Electrical Characteristics (Ta = 25°C)

Parameter				
Reverse breakdown voltage I_R = 50uA			420V	
Maximum forward voltage drop I_F	2%	V_F	1.0V	
Reverse Recovery Time I_F=0.5A, I_R=1A, I_{rr}=0.25A		Trr		
Maximum reverse current	$V_R = V_{RRM}$ 2%		2uA	0.05uA

Device Schematics and Outline Drawing

Die Thickness
Die Size *
Top Metal Pad
Active Area
Top Metal
Back Metal
Note: 1 *: Cutting street width is around 40um

Important Notice

Specification apply to die only. Actual performance may degrade when assembled.

Yangjie Electronics does not guarantee device performance after assembly.
All operating parameters must be validated for each customer application by customer's technical experts.

Data sheet information is subjected to change without notice.

Recommended Storage Environment:

Store in original container, in dessicated nitrogen, with no contamination.

Shelf life for parts stored in above condition is 2 years.

If the storage is done in normal atmosphere shelf life is reduced to 6 months.

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